BSR14,215 Datasheet

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DiGi Electronics Part Number	BSR14,215-DG
Manufacturer	Nexperia USA Inc.
Manufacturer Product Number	BSR14,215
Description	TRANS NPN 40V 0.8A TO236AB
Detailed Description	Bipolar (BJT) Transistor NPN 40 V 800 mA 300MHz 250 mW Surface Mount TO-236AB

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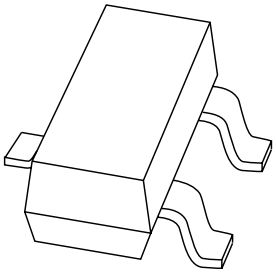
Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
BSR14,215	Nexperia USA Inc.
Series:	Product Status:
-	Active
Transistor Type:	Current - Collector (Ic) (Max):
NPN	800 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ Ib, Ic:
40 V	1V @ 50mA, 500mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
10nA (ICBO)	100 @ 150mA, 10V
Power - Max:	Frequency - Transition:
250 mW	300MHz
Operating Temperature:	Grade:
150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Package / Case:	Supplier Device Package:
TO-236-3, SC-59, SOT-23-3	TO-236AB
Base Product Number:	
BSR14	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0075	

DATA SHEET



BSR13; BSR14
NPN switching transistors

Product data sheet
Supersedes data of 1999 Apr 15

2004 Jan 13

NPN switching transistors BSR13; BSR14

FEATURES

- High current (max. 800 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- Switching and linear applications.

DESCRIPTION

NPN switching transistor in a SOT23 plastic package.
PNP complements: BSR15 and BSR16.

MARKING

TYPE NUMBER	MARKING CODE(1)
BSR13	U7*
BSR14	U8*

Note

1. * = p : Made in Hong Kong.
   * = t : Made in Malaysia.
   * = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

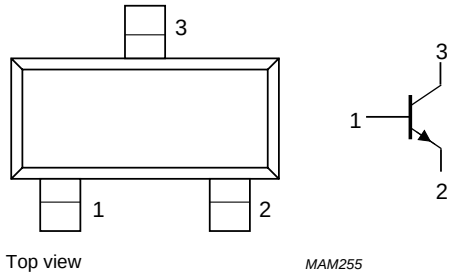


Fig.1 Simplified outline (SOT23) and symbol.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BSR13	–	plastic surface mounted package; 3 leads	SOT23
BSR14			

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BSR13		–	60	V
	BSR14		–	75	V
V_{CEO}	collector-emitter voltage	open base			
	BSR13		–	30	V
	BSR14		–	40	V
V_{EBO}	emitter-base voltage	open collector			
	BSR13		–	5	V
	BSR14		–	6	V
I_C	collector current (DC)		–	800	mA
I_{CM}	peak collector current		–	800	mA
I_{BM}	peak base current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	–	250	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

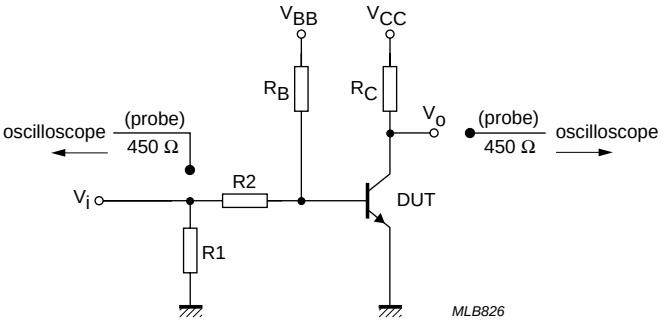
T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current				
	BSR13	$I_E = 0$; $V_{CB} = 50$ V	–	30	nA
		$I_E = 0$; $V_{CB} = 50$ V; $T_j = 150$ °C	–	10	μA
	collector cut-off current				
	BSR14	$I_E = 0$; $V_{CB} = 60$ V	–	10	nA
		$I_E = 0$; $V_{CB} = 60$ V; $T_j = 150$ °C	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = 5$ V			
	BSR13		–	30	nA
	BSR14		–	10	nA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
h_{FE}	DC current gain	I_C = 0.1 mA; V_{CE} = 10 V; note 1	35	–	
		I_C = 1 mA; V_{CE} = 10 V; note 1	50	–	
		I_C = 10 mA; V_{CE} = 10 V; note 1	75	–	
		I_C = 150 mA; V_{CE} = 10 V; note 1	100	300	
		I_C = 150 mA; V_{CE} = 1 V; note 1	50	–	
	DC current gain	I_C = 500 mA; V_{CE} = 10 V; note 1			
	BSR13		30	–	
	BSR14		40	–	
V_{CEsat}	collector-emitter saturation voltage	I_C = 150 mA; I_B = 15 mA			
	BSR13		–	400	mV
	BSR14		–	300	mV
	collector-emitter saturation voltage	I_C = 500 mA; I_B = 50 mA			
	BSR13		–	1.6	V
	BSR14		–	1	V
V_{BEsat}	base-emitter saturation voltage	I_C = 150 mA; I_B = 15 mA			
	BSR13		–	1.3	V
	BSR14		0.6	1.2	V
	base-emitter saturation voltage	I_C = 500 mA; I_B = 50 mA			
	BSR13		–	2.6	V
	BSR14		–	2	V
C_c	collector capacitance	$I_E = I_e$ = 0; V_{CB} = 10 V; f = 1 MHz	–	8	pF
f_T	transition frequency	I_C = 20 mA; V_{CE} = 20 V; f = 100 MHz			
	BSR13		250	–	MHz
	BSR14		300	–	MHz
Switching times (between 10% and 90% levels); see Fig.2					
t_{on}	turn-on time	I_{Con} = 150 mA; I_{Bon} = 15 mA; I_{Boff} = −15 mA	–	35	ns
t_d	delay time		–	15	ns
t_r	rise time		–	20	ns
t_{off}	turn-off time		–	250	ns
t_s	storage time		–	200	ns
t_f	fall time		–	60	ns

Note

1. Pulse test: $t_p \leq 300\ \mu s$; $\delta \leq 0.02$.

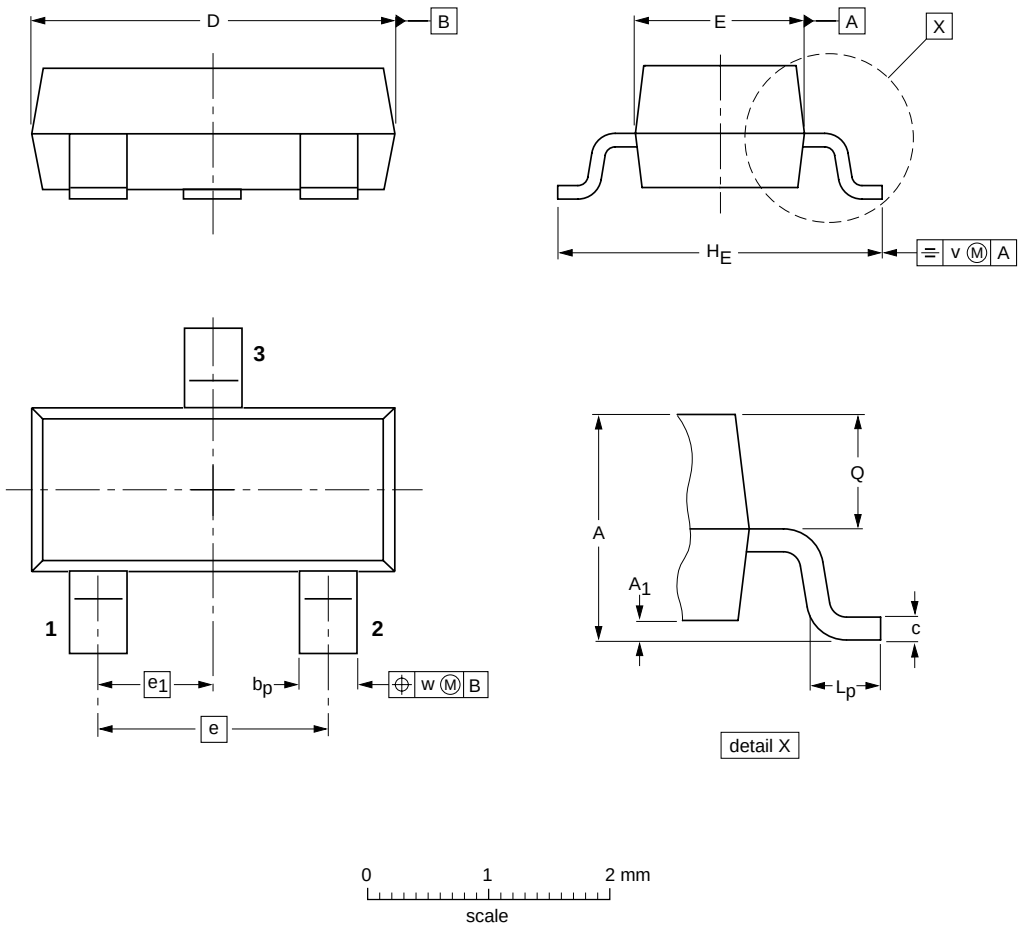


V_i = 9.5 V; T = 500 μs; t_p = 10 μs; $t_r = t_f \leq 3$ ns.
R1 = 68 Ω; R2 = 325 Ω; R_B = 325 Ω; R_C = 160 Ω.
V_{BB} = −3.5 V; V_{CC} = 29.5 V.
Oscilloscope: input impedance $Z_i = \geq 100$ Ω.

Fig.2 Test circuit for switching times.

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads **SOT23**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max.	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT23		TO-236AB				~~04-11-04~~ 06-03-16

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

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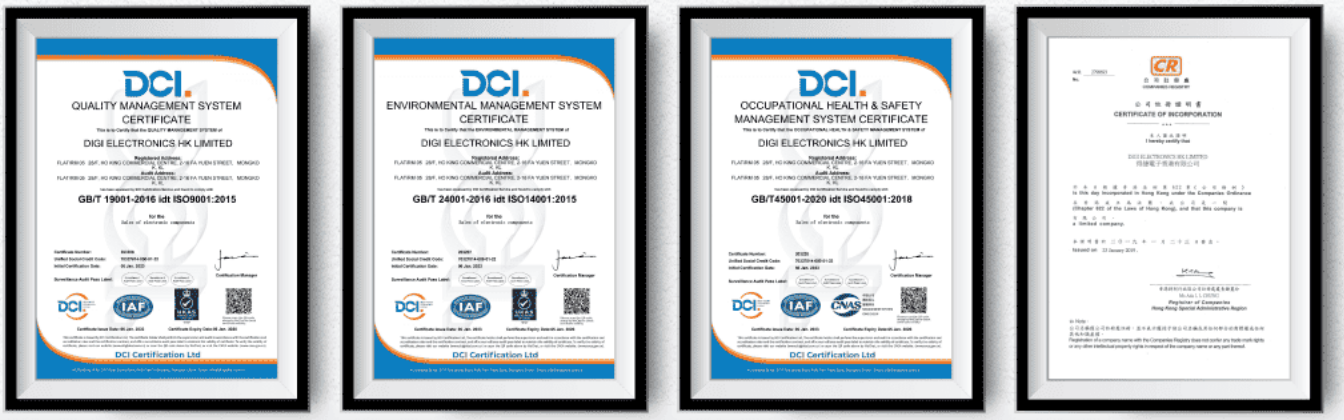

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